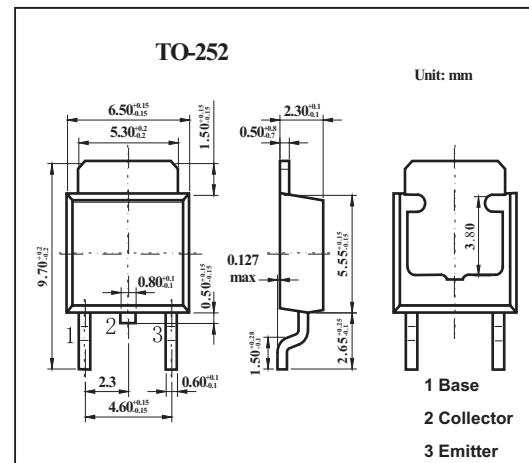


2SD992-Z

■ Features

- Low V_{CE(sat)}.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{C EO}	30	V
Emitter-base voltage	V _{EBO}	5	V
Collector current (DC)	I _C	2	A
Collector Current (pulse) *	I _{CP}	3	A
Total power dissipation	P _T	2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Pulse Test PW ≤ 10ms, Duty Cycle ≤ 50%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 20 V, I _E = 0			10	nA
DC current gain *	h _{FE}	V _{CE} = 0.5 V, I _C = 0.1 A	35		200	
		V _{CE} = 0.5 V, I _C = 2.0 A	50			
Collector saturation voltage *	V _{CE(sat)}	I _C = 2.0 A, I _B = 40 mA		0.3	0.5	V
Base saturation voltage *	V _{BE(sat)}	I _C = 2.0 A, I _B = 40 mA		0.95	1.5	V

* Pulsed: PW ≤ 350 µs, duty cycle ≤ 2%

■ hFE Classification

Marking	N	M	L	K
hFE	35~80	60~120	80~120	100~200